

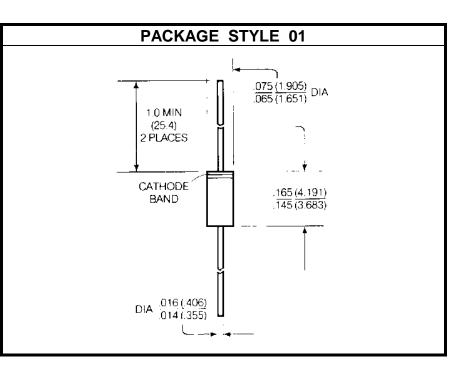
SILICON PIN DIODE CHIP

DESCRIPTION:

The **AP3000C-11** is a Passivated Epitaxial Silicon PIN Diode Housed in a Hermetically Sealed Glass Package. This Device is Designed to Cover a Wide Range of Control Applications Such as RF Switching, Phase Shifting, Modulation, Duplexing Limiting and Pulse Forming.

MAXIMUM RATINGS

I _F	100 mA					
V _R	300 V					
P _{DISS}	250 mW @ $T_A = 25 {}^{\circ}C$					
θ _{JC}	20 ⁰ C/W					



CHARACTERISTICS T_C = 25 °C

SYMBOL	TEST CONDITIONS			MINIMUM	TYPICAL	MAXIMUM	UNITS
V _{BR}	$I_R = 10 \ \mu A$			300			V
CJ	V _R = 50 V V _R = 40 V	f = 1.	.0 MHz			0.2	pF
Rs	I _F = 50 mA	f = 10	00 MHz			0.6	Ohms
TL	I _F =10 mA	I _R = 6.0 mA			1000		nS
T _{rr}	I _F =20 mA	I _R = 100 mA			100		nS

ADVANCED SEMICONDUCTOR, INC.

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